Switch-mode Schottky Power Rectifier

Surface Mount Power Package

MBRD5H100, NBRD5H100

This series of Power Rectifiers employs the Schottky Barrier principle in a large metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes, and polarity protection diodes.

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Short Heat Sink Tab Manufactured Not Sheared!
- NBRD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant*

Mechanical Characteristics:

- Case: Epoxy, Molded, Epoxy Meets UL 94 V-0
- Weight: 0.4 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Ratings:
 - Machine Model = C (> 400 V)
 - Human Body Model = 3B (> 8000 V)



ON Semiconductor®

www.onsemi.com

SCHOTTKY BARRIER RECTIFIER 5 AMPERES, 100 VOLTS



DPAK CASE 369C



(Pin 1: No Connect)

MARKING DIAGRAM



A = Assembly Location

Y = Year
WW = Work Week
B5100 = Device Code
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRD5H100T4G	DPAK (Pb-Free)	2,500 / Tape & Reel
NBRD5H100T4G	DPAK (Pb-Free)	2,500 / Tape & Reel
NBRD5H100T4G-VF01	DPAK (Pb-Free)	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBRD5H100, NBRD5H100

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	٧
Average Rectified Forward Current T _C = 171°C	I _{F(AV)}	5	Α
Peak Repetitive Forward Current (Square Wave, Duty = 0.5) T _C = 171°C	I _{FRM}	10	Α
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	105	Α
Operating Junction and Storage Temperature Range (Note 1)	T _J , T _{stg}	-65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction-to-Case (Note 2) Junction-to-Ambient (Note 2)	R _{θJC} R _{θJA}	1.6 95.8	°C/W

^{2.} When mounted using minimum recommended pad size on FR-4 board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) $(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$ $(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$	V _F	0.71 0.60	٧
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, $T_J = 125^{\circ}C$) (Rated dc Voltage, $T_J = 25^{\circ}C$)	I _R	4.5 3.5	mA μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{3.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

MBRD5H100, NBRD5H100

TYPICAL CHARACTERISTICS

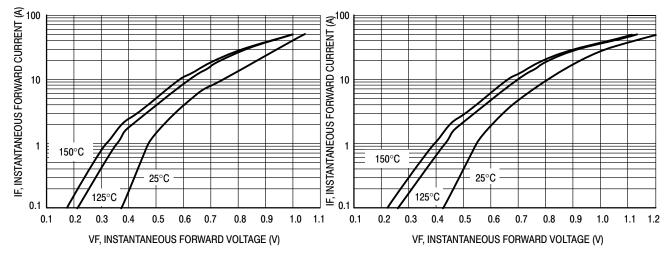


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

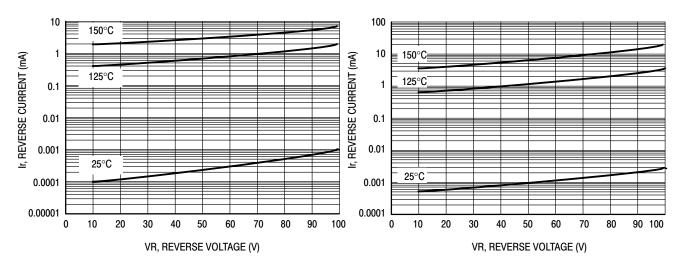


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

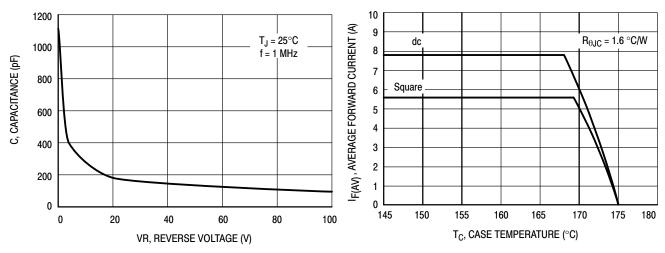
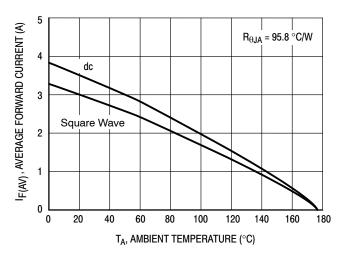


Figure 5. Typical Capacitance

Figure 6. Current Derating, Case

MBRD5H100, NBRD5H100

TYPICAL CHARACTERISTICS



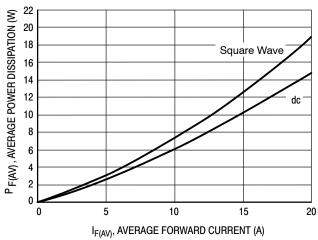


Figure 7. Current Derating, Ambient

Figure 8. Forward Power Dissipation

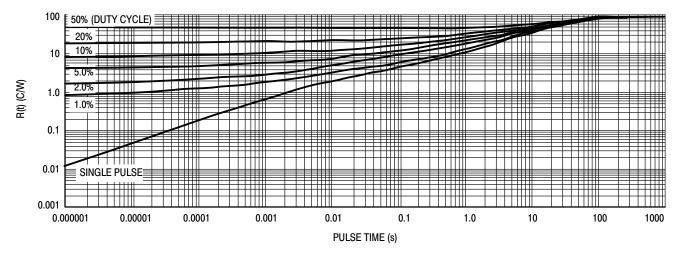
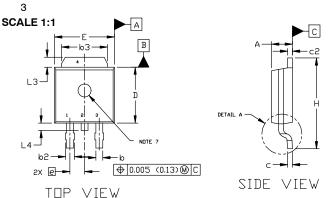


Figure 9. Thermal Response, Junction-to-Case

DPAK (SINGLE GAUGE)

CASE 369C ISSUE G

DATE 31 MAY 2023

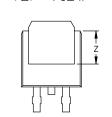


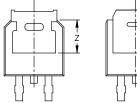


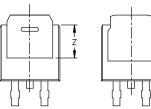
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE DUTERMOST EXTREMES OF THE PLASTIC BODY.

 DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90	REF
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	





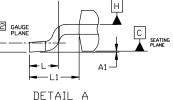


BOTTOM VIEW

5.80

BOTTOM VIEW ALTERNATE

CONSTRUCTIONS [0.228] 6.20 L2 GAUGE PLANE [0.244] 2.58 3.00 [0.102] [0.118] 1.60 [0.063] 6.17



STYLE 5: PIN 1. GATE

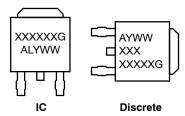
2. ANODE

3 CATHODE

ANODE

CW ROTATED 90°

GENERIC MARKING DIAGRAM*



= Device Code
= Assembly Location
= Wafer Lot
= Year
= Work Week
= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT* *FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

[0.243]

STYLE 1: PIN 1. BASE STYLE 2: PIN 1. GATE STYLE 3: PIN 1. ANODE STYLE 4: PIN 1. CATHODE 2. COLLECTOR 2. DRAIN 2. CATHODE 2. ANODE 3 SOURCE 3 FMITTER 3 ANODE 3 GATE

COLLECTOR 4. DRAIN 4. CATHODE 4. ANODE STYLE 6: STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 8: STYLE 9: PIN 1. MT1 2. MT2

STYLE 10: PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE PIN 1. CATHODE 2. ANODE 3 CATHODE 3 FMITTER 3 RESISTOR ADJUST 4. COLLECTOR 4. CATHODE 4. ANODE CATHODE

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

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3 GATE

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